

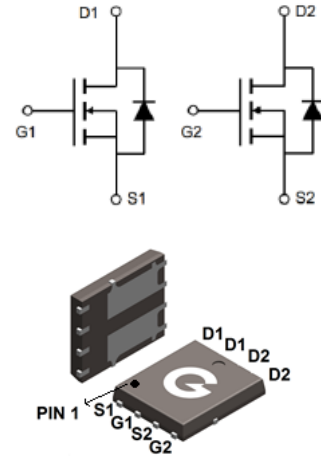
Features

- Super low gate charge
- Green device available
- Excellent C_{dv} / d_t effect decline
- Advanced high cell density trench technology
- Halogen free
- Qualified to AEC-Q101 standards for high reliability

HF

Mechanical Data

- Case: PDFN5×6-8LC
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



PDFN5×6-8LC

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
TGBLN6601-5DL8	PDFN5×6-8LC	5000 pcs / Tape & Reel	GBLN6601

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	60	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_C = 25^\circ\text{C}$) ^{*1}	I_D	25	A
Continuous Drain Current ($T_C = 100^\circ\text{C}$) ^{*1}		18	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	98	A
Single Pulse Avalanche Energy ^{*3}	E_{AS}	40	mJ

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation ($T_C = 25^\circ\text{C}$) ^{*4}	P_D	33	W
Thermal Resistance Junction-to-Case ^{*1}	$R_{\theta JC}$	4.5	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Air ^{*5}	$R_{\theta JA}$	100	$^\circ\text{C/W}$
Operating Junction Temperature Range	T_J	$-55 \sim +175$	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	$-55 \sim +175$	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 48V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
R _{DS(ON)}	Static Drain-Source On-resistance *2	V _{GS} = 10V,I _D = 20A	-	12	20	mΩ
		V _{GS} = 4.5V,I _D = 15A	-	16	24	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1	1.7	2.5	V
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V V _{DS} = 15V f = 1.0MHz	-	1880	-	pF
C _{OSS}	Output Capacitance		-	170	-	
C _{RSS}	Reverse Transfer Capacitance		-	140	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time	V _{DD} = 30V V _{GS} = 10V R _G =3Ω I _D = 15A	-	7.4	-	ns
t _r	Turn-on Rise Time		-	5.1	-	
t _{d(OFF)}	Turn-Off Delay Time		-	28.3	-	
t _f	Turn-Off Fall Time		-	5.5	-	
Q _G	Total Gate-Charge	V _{DD} = 48V V _{GS} = 10V I _D = 15A	-	36	-	nC
Q _{GS}	Gate to Source Charge		-	4.7	-	
Q _{GD}	Gate to Drain (Miller) Charge		-	9	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *2	I _{SD} = 5A, V _{GS} = 0V, T _J = 25°C	-	-	1.2	V
I _S	Diode Continuous Forward Current *1,4		-	-	25	A
trr	Reverse Recovery Time	V _R =50V, I _F = 15A	-	26	-	ns
Qrr	Reverse Recovery Charge	di/dt = 100A/μs	-	18	-	nC

Notes:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.1mH$
- The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation
- The data is test on minimal footprint

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

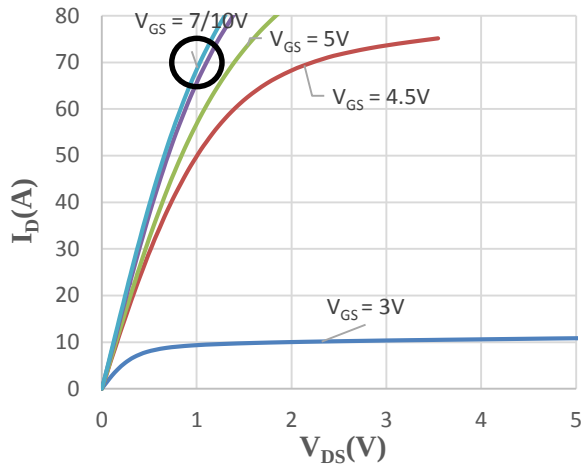


Fig 1 Output Characteristics

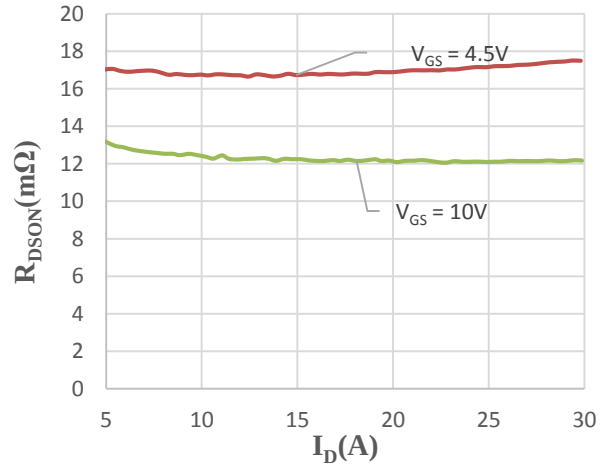


Fig 2 On-Resistance vs. Drain Current

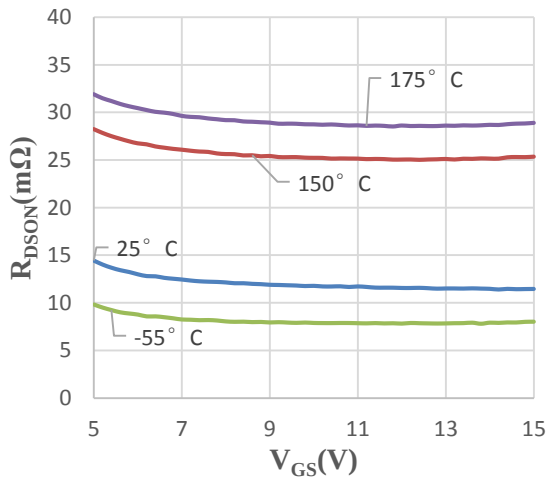


Fig 3 On-Resistance vs. Gate-Source Voltage

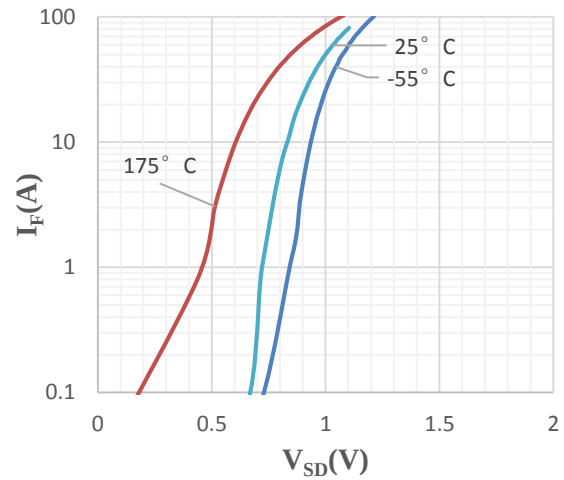


Fig 4 Body-Diode Characteristics

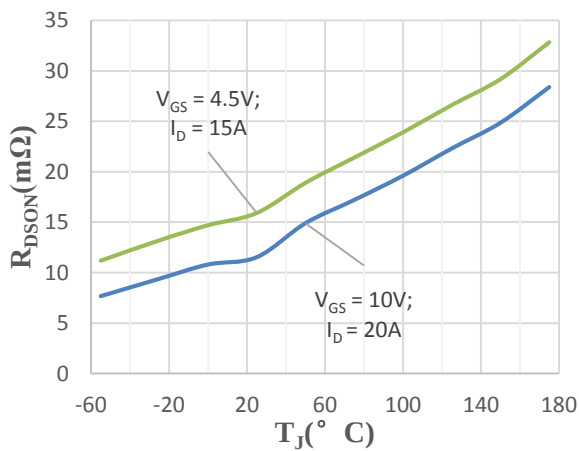


Fig 5 On-Resistance vs. Junction Temperature

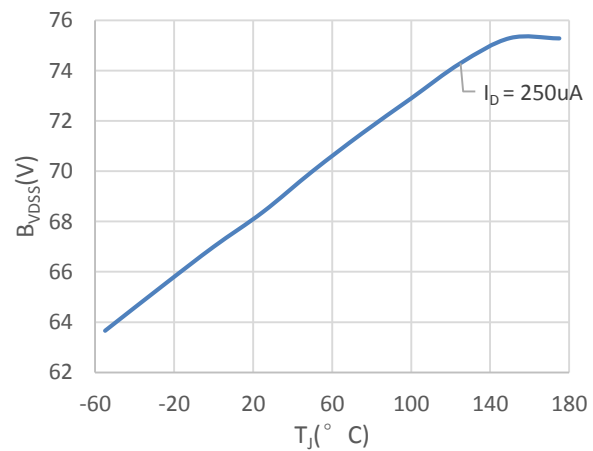


Fig 6 Drain-Source vs. Junction Temperature

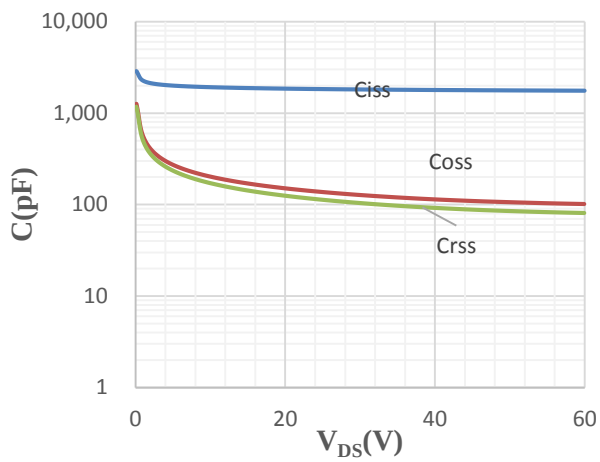


Fig 7 Capacitance Characteristics

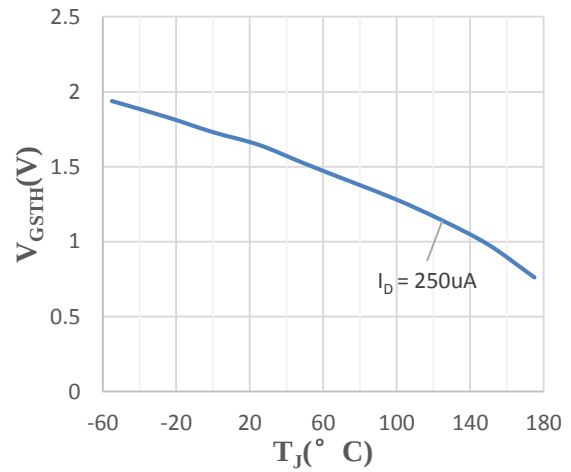


Fig 8 Gate Voltage vs. Junction Temperature

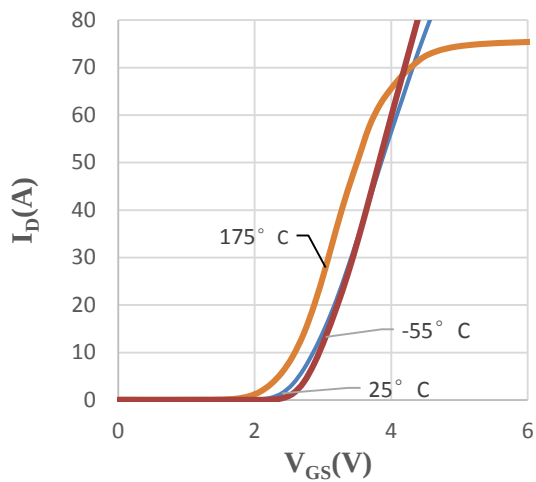


Fig 9 Transfer Characteristics

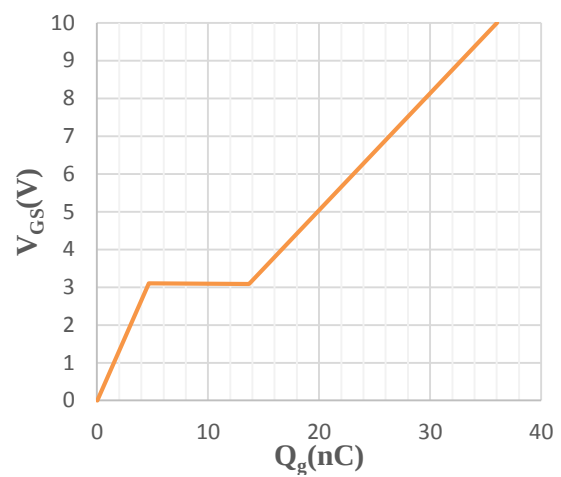
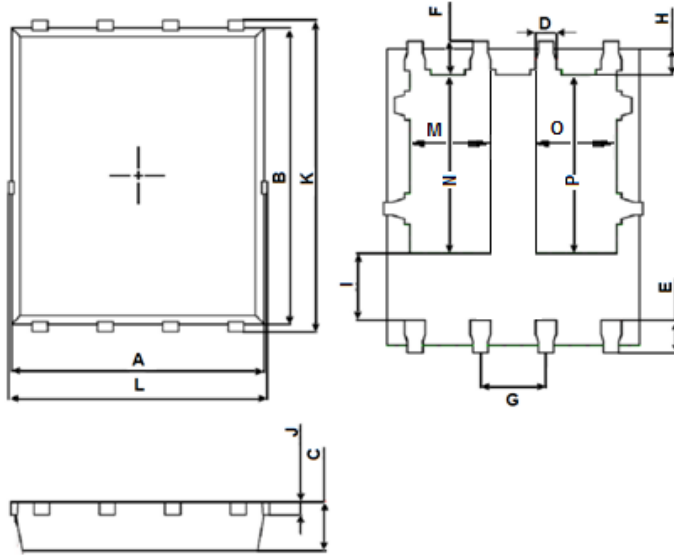


Fig 10 Gate-Charge Characteristics

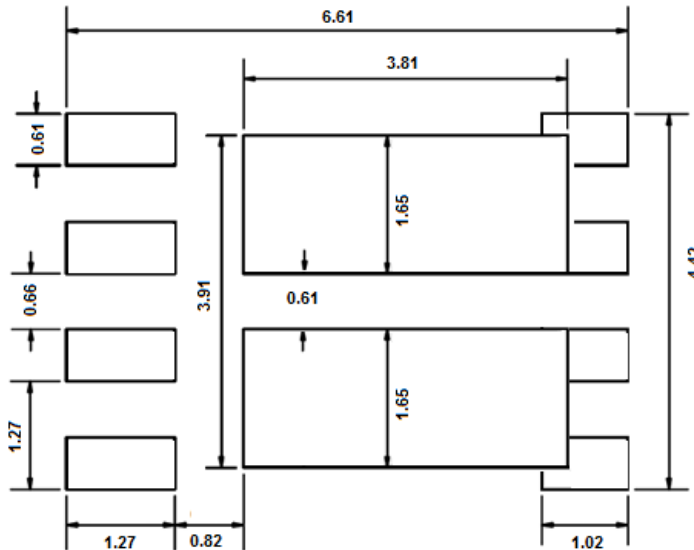
Package Outline Dimensions (Unit: mm)



PDFN5x6-8LC		
Dimension	Min.	Max.
A	4.824	4.976
B	5.674	5.826
C	0.900	1.000
D	0.350	0.450
E	0.559	0.711
F	0.574	0.726
G	1.250	1.290
H	0.424	0.576
I	1.190	1.390
J	0.154	0.354
K	5.974	6.126
L	4.944	5.096
M/O	1.595	1.795
N/P	3.375	3.575

Mounting Pad Layout (Unit: mm)

PDFN5x6-8LC



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